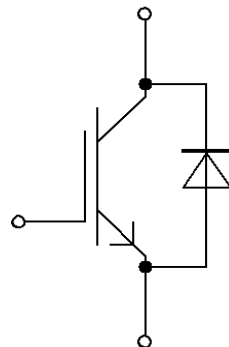


62mm C-Series 模块 采用第四代沟槽栅/场终止IGBT4和第四代发射极控制二极管  
 62mm C-Series module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode



$V_{CES} = 1200V$   
 $I_{C\ nom} = 900A / I_{CRM} = 1800A$

### 典型应用

- 大功率变流器
- 电机传动
- UPS系统
- 风力发电机

### 电气特性

- 提高工作结温  $T_{vj\ op}$
- 低  $V_{CESat}$
- 无与伦比的坚固性
- $V_{CESat}$  带正温度系数

### 机械特性

- 4 kV 交流 1分钟 绝缘
- 封装的 CTI > 400
- 高爬电距离和电气间隙
- 高功率密度
- 绝缘的基板
- 标准封装

### Typical Applications

- High power converters
- Motor drives
- UPS systems
- Wind turbines

### Electrical Features

- Extended operating temperature  $T_{vj\ op}$
- Low  $V_{CESat}$
- Unbeatable robustness
- $V_{CESat}$  with positive temperature coefficient

### Mechanical Features

- 4 kV AC 1min insulation
- Package with CTI > 400
- High creepage and clearance distances
- High power density
- Isolated base plate
- Standard housing

## Module Label Code

Barcode Code 128



DMX - Code



### Content of the Code

| Content of the Code        | Digit   |
|----------------------------|---------|
| Module Serial Number       | 1 - 5   |
| Module Material Number     | 6 - 11  |
| Production Order Number    | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

## IGBT, 逆变器 / IGBT, Inverter

## 最大额定值 / Maximum Rated Values

|                                                |                                                                     |                    |       |   |
|------------------------------------------------|---------------------------------------------------------------------|--------------------|-------|---|
| 集电极 - 发射极电压<br>Collector-emitter voltage       | $T_{vj} = 25^{\circ}\text{C}$                                       | $V_{CES}$          | 1200  | V |
| 连续集电极直流电流<br>Continuous DC collector current   | $T_C = 95^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$ | $I_{C\text{ nom}}$ | 900   | A |
| 集电极重复峰值电流<br>Repetitive peak collector current | $t_P = 1\text{ ms}$                                                 | $I_{CRM}$          | 1800  | A |
| 栅极 - 发射极峰值电压<br>Gate-emitter peak voltage      |                                                                     | $V_{GES}$          | +/-20 | V |

## 特征值 / Characteristic Values

|                                                       |                                                                                                                                                                                             |                                                                                                   | min.                | typ.                 | max.   |                                                 |
|-------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|---------------------|----------------------|--------|-------------------------------------------------|
| 集电极 - 发射极饱和电压<br>Collector-emitter saturation voltage | $I_C = 900\text{ A}, V_{GE} = 15\text{ V}$<br>$I_C = 900\text{ A}, V_{GE} = 15\text{ V}$<br>$I_C = 900\text{ A}, V_{GE} = 15\text{ V}$                                                      | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{ sat}}$ | 1,70<br>2,00<br>2,10 | 2,05   | V<br>V<br>V                                     |
| 栅极阈值电压<br>Gate threshold voltage                      | $I_C = 32,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                        |                                                                                                   | $V_{GEth}$          | 5,20                 | 5,80   | 6,40 V                                          |
| 栅极电荷<br>Gate charge                                   | $V_{GE} = -15\text{ V} \dots +15\text{ V}$                                                                                                                                                  |                                                                                                   | $Q_G$               | 7,40                 |        | $\mu\text{C}$                                   |
| 内部栅极电阻<br>Internal gate resistor                      | $T_{vj} = 25^{\circ}\text{C}$                                                                                                                                                               |                                                                                                   | $R_{Gint}$          | 0,9                  |        | $\Omega$                                        |
| 输入电容<br>Input capacitance                             | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$                                                                                                  |                                                                                                   | $C_{ies}$           | 56,0                 |        | nF                                              |
| 反向传输电容<br>Reverse transfer capacitance                | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$                                                                                                  |                                                                                                   | $C_{res}$           | 2,20                 |        | nF                                              |
| 集电极-发射极截止电流<br>Collector-emitter cut-off current      | $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                  |                                                                                                   | $I_{CES}$           |                      | 5,0    | mA                                              |
| 栅极-发射极漏电流<br>Gate-emitter leakage current             | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                    |                                                                                                   | $I_{GES}$           |                      | 400    | nA                                              |
| 开通延迟时间(电感负载)<br>Turn-on delay time, inductive load    | $I_C = 900\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Gon} = 1,5\ \Omega$                                                                                        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_{don}$           | 0,24<br>0,25<br>0,26 |        | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| 上升时间(电感负载)<br>Rise time, inductive load               | $I_C = 900\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Gon} = 1,5\ \Omega$                                                                                        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_r$               | 0,09<br>0,10<br>0,11 |        | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| 关断延迟时间(电感负载)<br>Turn-off delay time, inductive load   | $I_C = 900\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Goff} = 0,9\ \Omega$                                                                                       | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_{doff}$          | 0,61<br>0,64<br>0,66 |        | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| 下降时间(电感负载)<br>Fall time, inductive load               | $I_C = 900\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Goff} = 0,9\ \Omega$                                                                                       | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_f$               | 0,14<br>0,17<br>0,18 |        | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| 开通损耗能量(每脉冲)<br>Turn-on energy loss per pulse          | $I_C = 900\text{ A}, V_{CE} = 600\text{ V}, L_S = 60\text{ nH}$<br>$V_{GE} = \pm 15\text{ V}, di/dt = 6000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$<br>$R_{Gon} = 1,5\ \Omega$  | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $E_{on}$            | 40,0<br>55,0<br>60,0 |        | mJ<br>mJ<br>mJ                                  |
| 关断损耗能量(每脉冲)<br>Turn-off energy loss per pulse         | $I_C = 900\text{ A}, V_{CE} = 600\text{ V}, L_S = 60\text{ nH}$<br>$V_{GE} = \pm 15\text{ V}, du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$<br>$R_{Goff} = 0,9\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $E_{off}$           | 110<br>160<br>175    |        | mJ<br>mJ<br>mJ                                  |
| 短路数据<br>SC data                                       | $V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$<br>$V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$                                                                                             | $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$                                          | $I_{SC}$            | 3600                 |        | A                                               |
| 结 - 外壳热阻<br>Thermal resistance, junction to case      | 每个 IGBT / per IGBT                                                                                                                                                                          |                                                                                                   | $R_{thJC}$          |                      | 0,0310 | K/W                                             |
| 外壳 - 散热器热阻<br>Thermal resistance, case to heatsink    | 每个 IGBT / per IGBT<br>$\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$                                          |                                                                                                   | $R_{thCH}$          | 0,0180               |        | K/W                                             |
| 在开关状态下温度<br>Temperature under switching conditions    |                                                                                                                                                                                             |                                                                                                   | $T_{vj\text{ op}}$  | -40                  | 150    | $^{\circ}\text{C}$                              |

## 二极管, 逆变器 / Diode, Inverter

### 最大额定值 / Maximum Rated Values

|                                             |                                                                                                                                              |           |                |                                              |
|---------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|-----------|----------------|----------------------------------------------|
| 反向重复峰值电压<br>Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$                                                                                                                | $V_{RRM}$ | 1200           | V                                            |
| 连续正向直流电流<br>Continuous DC forward current   |                                                                                                                                              | $I_F$     | 900            | A                                            |
| 正向重复峰值电流<br>Repetitive peak forward current | $t_P = 1\text{ ms}$                                                                                                                          | $I_{FRM}$ | 1800           | A                                            |
| $I_{2t}$ -值<br>$I_{2t}$ - value             | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$<br>$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | $I_{2t}$  | 91000<br>88000 | $\text{A}^2\text{s}$<br>$\text{A}^2\text{s}$ |

### 特征值 / Characteristic Values

|                                                    |                                                                                                                                                   |                                                                                                   | min.               | typ.                 | max.   |                                                 |
|----------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|--------------------|----------------------|--------|-------------------------------------------------|
| 正向电压<br>Forward voltage                            | $I_F = 900\text{ A}, V_{GE} = 0\text{ V}$<br>$I_F = 900\text{ A}, V_{GE} = 0\text{ V}$<br>$I_F = 900\text{ A}, V_{GE} = 0\text{ V}$               | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $V_F$              | 1,90<br>1,85<br>1,80 | 2,45   | V<br>V<br>V                                     |
| 反向恢复峰值电流<br>Peak reverse recovery current          | $I_F = 900\text{ A}, -di_F/dt = 6000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$<br>$V_R = 600\text{ V}$<br>$V_{GE} = -15\text{ V}$        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $I_{RM}$           | 540<br>720<br>750    |        | A<br>A<br>A                                     |
| 恢复电荷<br>Recovered charge                           | $I_F = 900\text{ A}, -di_F/dt = 6000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$<br>$V_R = 600\text{ V}$<br>$V_{GE} = -15\text{ V}$        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $Q_r$              | 80,0<br>150<br>180   |        | $\mu\text{C}$<br>$\mu\text{C}$<br>$\mu\text{C}$ |
| 反向恢复损耗 (每脉冲)<br>Reverse recovery energy            | $I_F = 900\text{ A}, -di_F/dt = 6000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$<br>$V_R = 600\text{ V}$<br>$V_{GE} = -15\text{ V}$        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $E_{rec}$          | 40,0<br>75,0<br>85,0 |        | mJ<br>mJ<br>mJ                                  |
| 结 - 外壳热阻<br>Thermal resistance, junction to case   | 每个二极管 / per diode                                                                                                                                 |                                                                                                   | $R_{thJC}$         |                      | 0,0560 | K/W                                             |
| 外壳 - 散热器热阻<br>Thermal resistance, case to heatsink | 每个二极管 / per diode<br>$\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ |                                                                                                   | $R_{thCH}$         | 0,0220               |        | K/W                                             |
| 在开关状态下温度<br>Temperature under switching conditions |                                                                                                                                                   |                                                                                                   | $T_{vj\text{ op}}$ | -40                  | 150    | $^{\circ}\text{C}$                              |

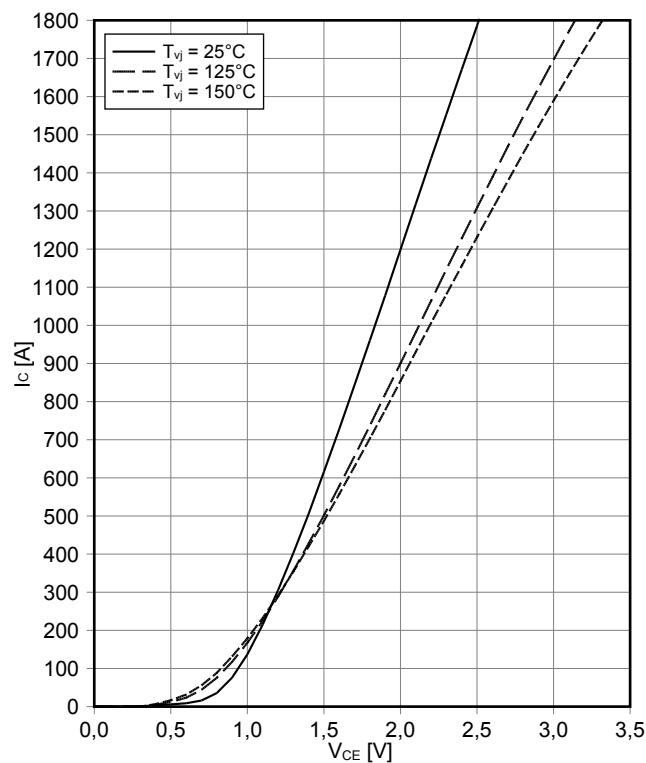
### 模块 / Module

|                                                          |                                                                                                                                                                  |                      |                                |             |
|----------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|--------------------------------|-------------|
| 绝缘测试电压<br>Isolation test voltage                         | RMS, f = 50 Hz, t = 1 min.                                                                                                                                       | V <sub>ISOL</sub>    | 4,0                            | kV          |
| 模块基板材料<br>Material of module baseplate                   |                                                                                                                                                                  |                      | Cu                             |             |
| 内部绝缘<br>Internal isolation                               | 基本绝缘 (class 1, IEC 61140)<br>basic insulation (class 1, IEC 61140)                                                                                               |                      | Al <sub>2</sub> O <sub>3</sub> |             |
| 爬电距离<br>Creepage distance                                | 端子至散热器 / terminal to heatsink<br>端子至端子 / terminal to terminal                                                                                                    |                      | 25,0<br>19,0                   | mm          |
| 电气间隙<br>Clearance                                        | 端子至散热器 / terminal to heatsink<br>端子至端子 / terminal to terminal                                                                                                    |                      | 25,0<br>10,0                   | mm          |
| 相对电痕指数<br>Comperative tracking index                     |                                                                                                                                                                  | CTI                  | > 400                          |             |
| min. typ. max.                                           |                                                                                                                                                                  |                      |                                |             |
| 杂散电感,模块<br>Stray inductance module                       |                                                                                                                                                                  | L <sub>sCE</sub>     | 16                             | nH          |
| 模块引线电阻,端子-芯片<br>Module lead resistance, terminals - chip | T <sub>C</sub> = 25°C, 每个开关 / per switch                                                                                                                         | R <sub>CC'+EE'</sub> | 0,50                           | mΩ          |
| 储存温度<br>Storage temperature                              |                                                                                                                                                                  | T <sub>stg</sub>     | -40                            | 125 °C      |
| 模块安装的安装扭矩<br>Mounting torque for modul mounting          | 螺丝 M6 根据相应的应用手册进行安装<br>Screw M6 - Mounting according to valid application note                                                                                   | M                    | 3,00                           | 6,00 Nm     |
| 端子联接扭矩<br>Terminal connection torque                     | 螺丝 M4 根据相应的应用手册进行安装<br>Screw M4 - Mounting according to valid application note<br>螺丝 M6 根据相应的应用手册进行安装<br>Screw M6 - Mounting according to valid application note | M                    | 1,1<br>2,5                     | -<br>5,0 Nm |
| 重量<br>Weight                                             |                                                                                                                                                                  | G                    | 340                            | g           |

## 输出特性 IGBT, 逆变器 (典型)

### output characteristic IGBT, Inverter (typical)

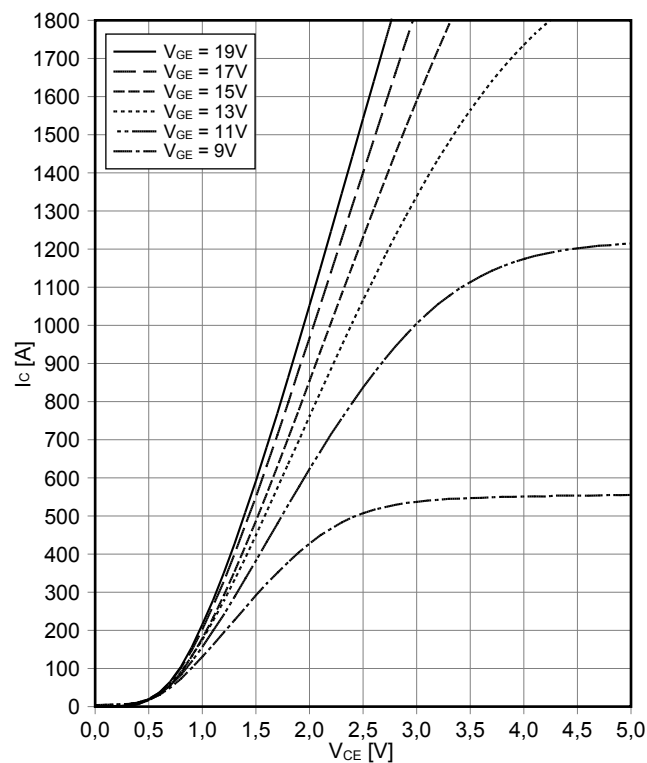
$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



## 输出特性 IGBT, 逆变器 (典型)

### output characteristic IGBT, Inverter (typical)

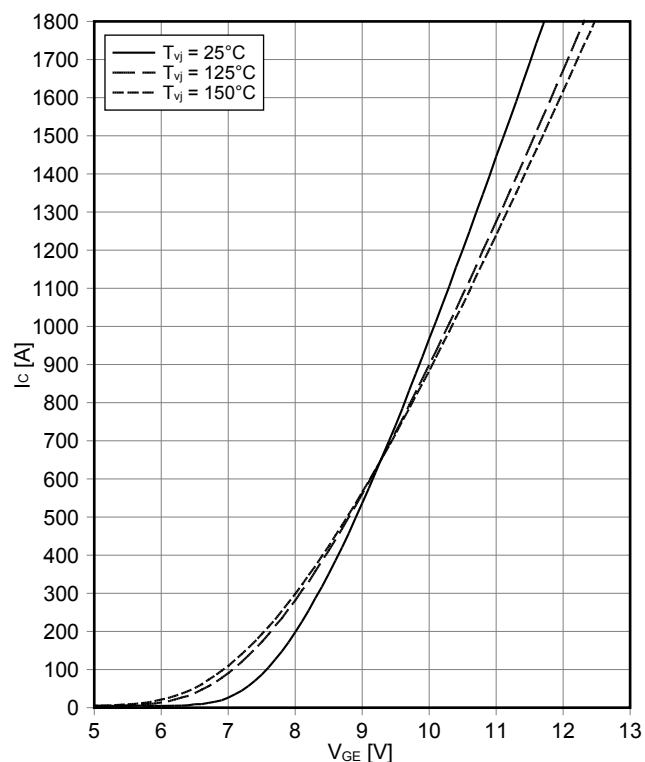
$I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



## 传输特性 IGBT, 逆变器 (典型)

### transfer characteristic IGBT, Inverter (typical)

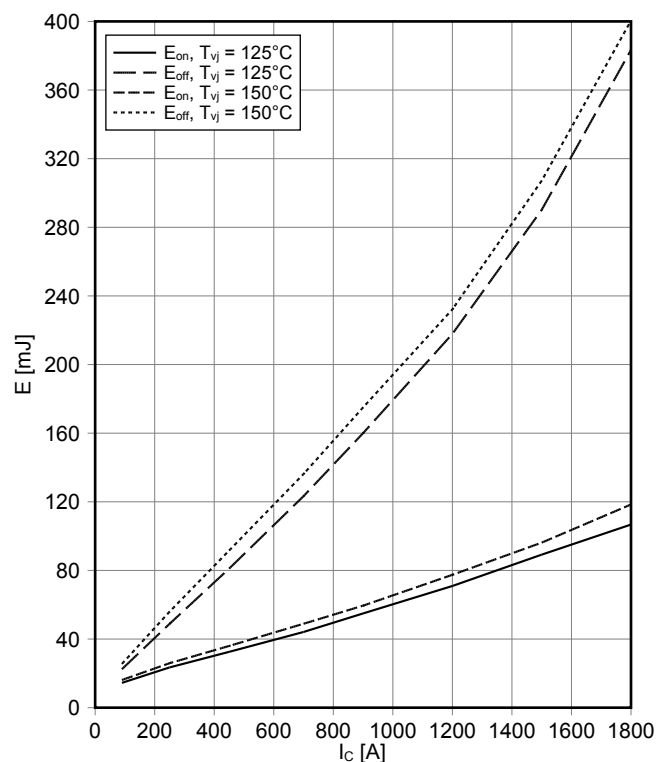
$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



## 开关损耗 IGBT, 逆变器 (典型)

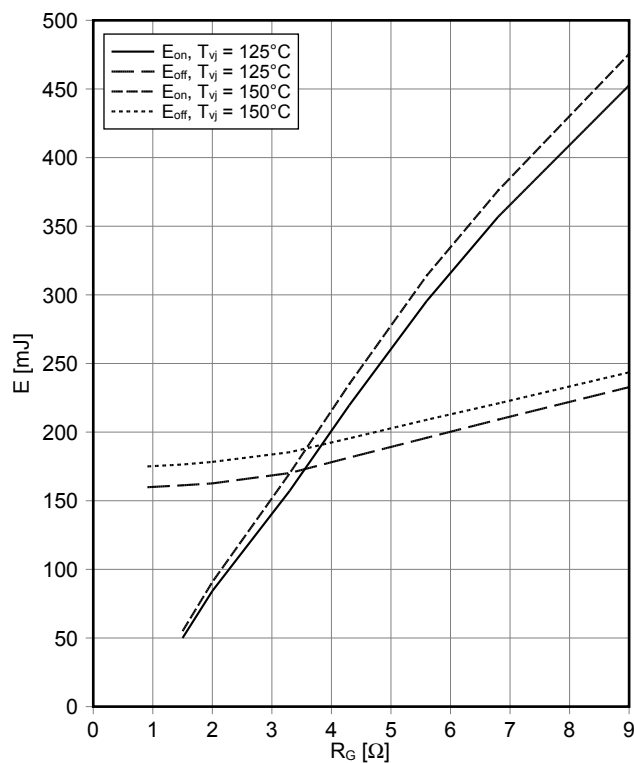
### switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 1.5\ \Omega$ ,  $R_{Goff} = 0.9\ \Omega$ ,  $V_{CE} = 600\text{ V}$



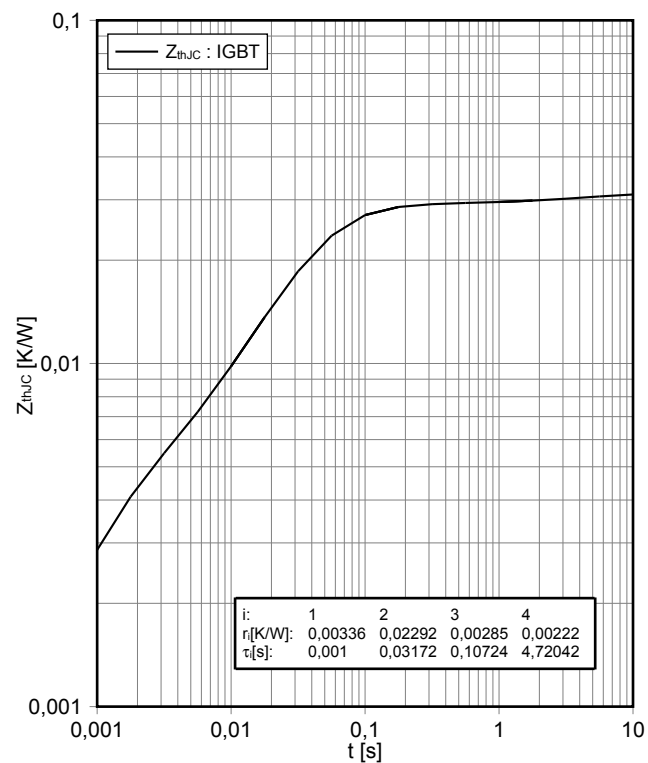
## 开关损耗 IGBT, 逆变器 (典型) switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15 \text{ V}$ ,  $I_C = 900 \text{ A}$ ,  $V_{CE} = 600 \text{ V}$



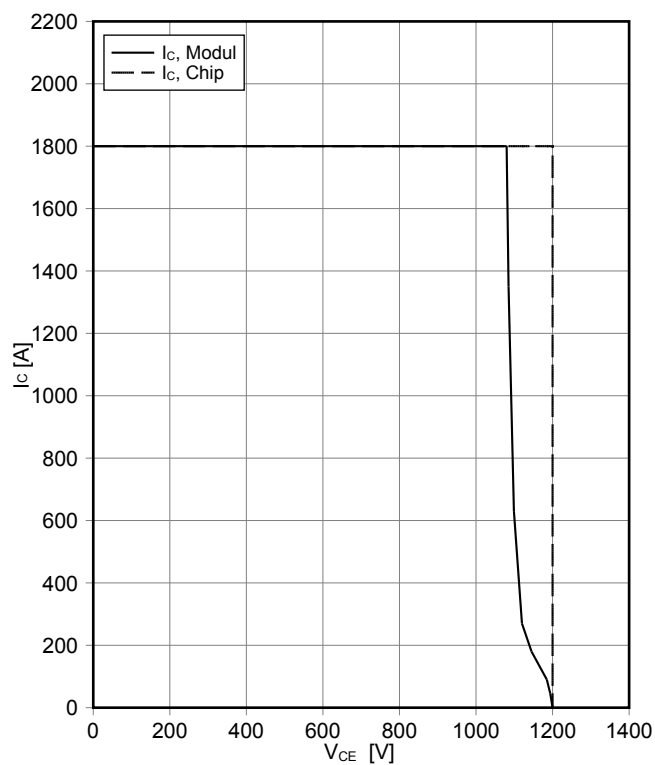
## 瞬态热阻抗 IGBT, 逆变器 transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



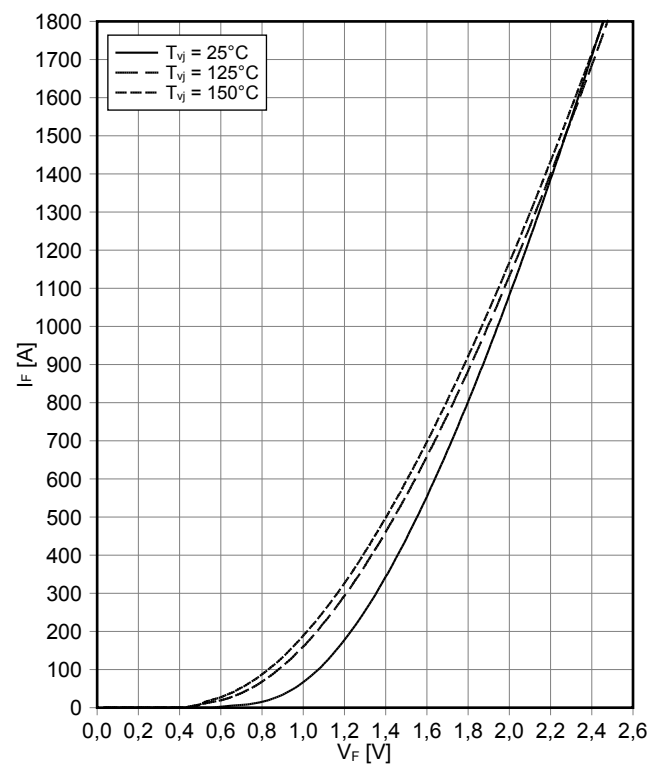
## 反偏安全工作区 IGBT, 逆变器 (RBSOA) reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15 \text{ V}$ ,  $R_{Goff} = 0.9 \Omega$ ,  $T_{vj} = 150^\circ\text{C}$



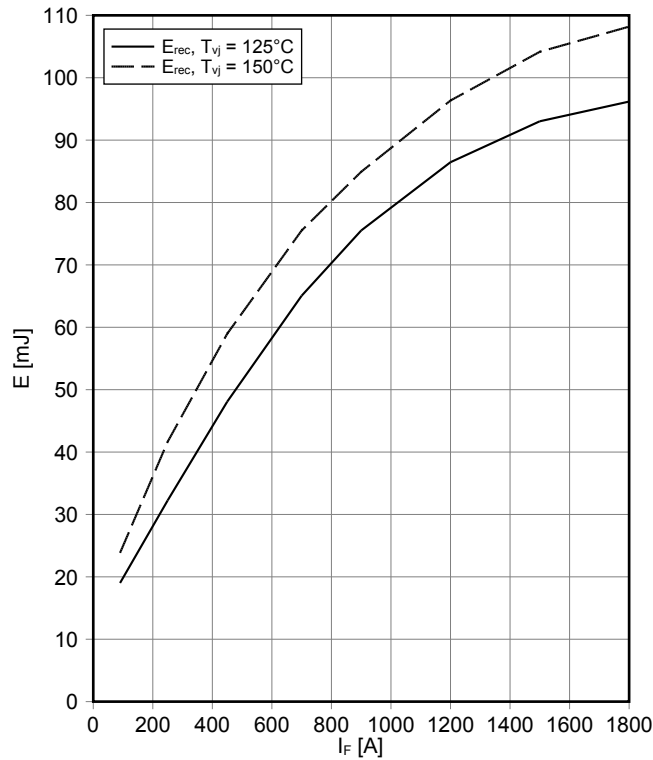
## 正向偏压特性 二极管, 逆变器 (典型) forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



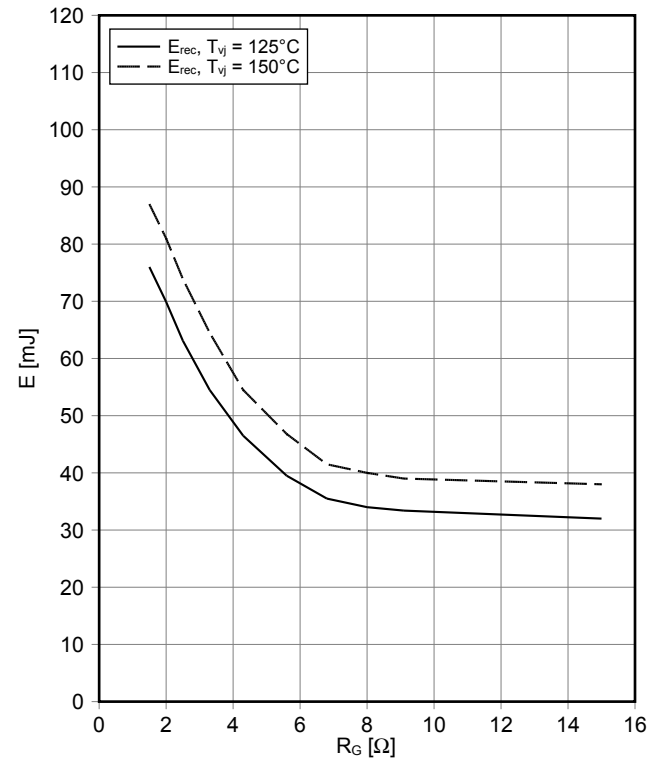
## 开关损耗 二极管,逆变器 (典型) switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 1.5 \Omega$ ,  $V_{CE} = 600 V$



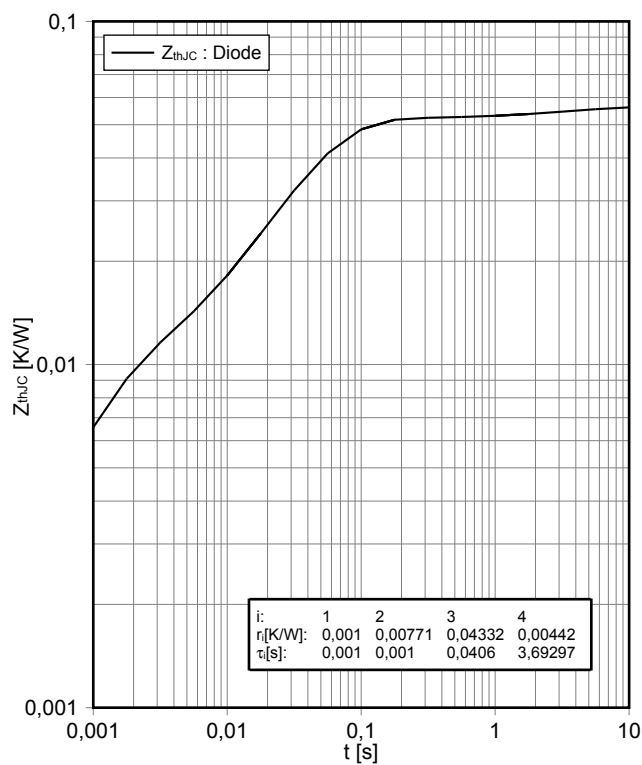
## 开关损耗 二极管,逆变器 (典型) switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$   
 $I_F = 900 A$ ,  $V_{CE} = 600 V$

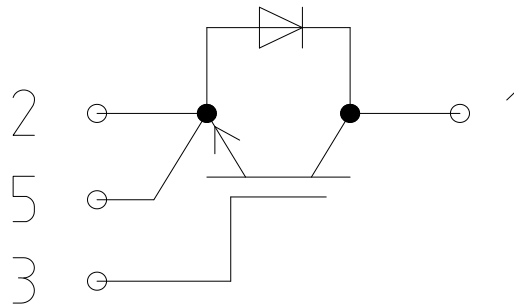


## 瞬态热阻抗 二极管,逆变器 transient thermal impedance Diode, Inverter

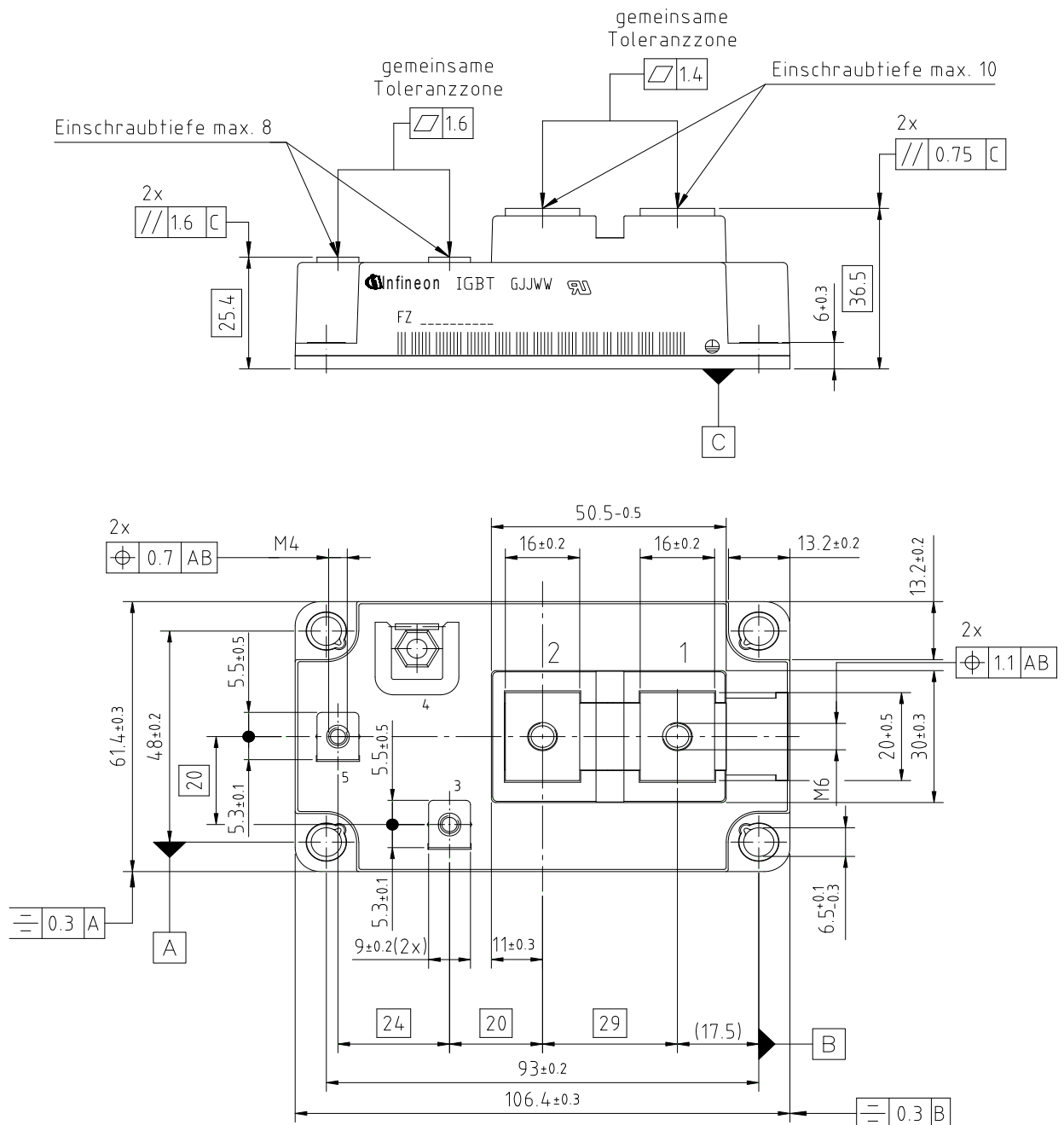
$Z_{thJC} = f(t)$



## 接线图 / Circuit diagram



## 封装尺寸 / Package outlines



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